

Product Summary

Symbol	Value	Unit
$I_{T(AV)}$	2.0	A
$V_{DRM} V_{RRM}$	600	V
I_{GT}	200	μA

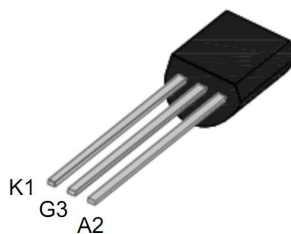
Feature

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

Application

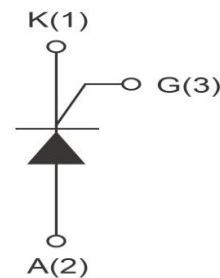
Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.

Package

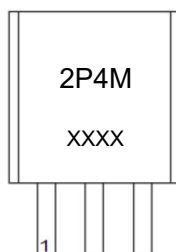


TO-92

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600	V
Repetitive peak reverse voltage	V_{RRM}	600	V
RMS on-state current	$I_{T(RMS)}$	3	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	20	A
I^2t value for fusing (tp=10ms)	I^2t	2	A ² s
Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$)	di_T/dt	50	A/ μ s
Peak gate current	I_{GM}	0.2	A
Average gate power dissipation	$P_{G(AV)}$	0.1	W
Junction Temperature	T_J	-40 ~ +110	°C
Storage Temperature	T_{STG}	-40 ~ +150	°C

Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value		Unit
				Min	Max	
Gate trigger current	I _{GT}	V _D =12V I _T =10mA T _j =25℃		10	200	μA
Gate trigger voltage	V _{GT}			-	0.8	V
Gate non-trigger voltage	V _{GD}	V _D =1/2V _{DRM} T _j =110℃		0.2	-	V
latching current	I _L	V _D =12V I _G =0.5mA R _{GK} =1kΩ T _j =25℃		-	3	mA
Holding current	I _H			-	4	mA
Critical-rate of rise of commutation voltage	dV _D /dt	V _D =2/3V _{DRM} Gate Open T _j =110℃		10	-	V/μs
STATIC CHARACTERISTICS						
Forward "on" voltage	V _{TM}	I _{TM} =4A tp=380μs		-	1.55	V
Repetitive Peak Off-State Current	I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25℃	-	5	μA
Repetitive Peak Reverse Current	I _{RRM}		T _j =110℃	-	0.1	mA
THERMAL RESISTANCES						
Thermal resistance	Rth(j-c)	Junction to case		TYP.	60	℃/W
	Rth(j-a)	Junction to ambient		TYP.	150	℃/W

Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

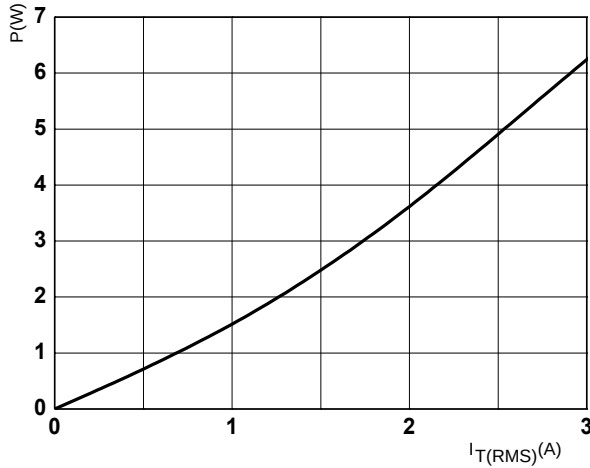


FIG.2: RMS on-state current versus case temperature (full cycle)

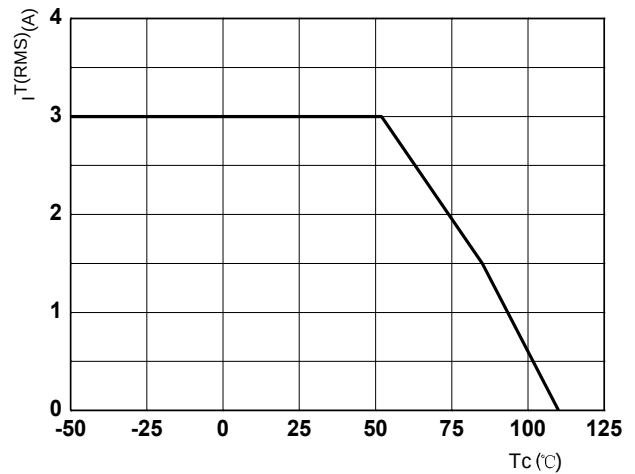


FIG.3: Surge peak on-state current versus number of cycles

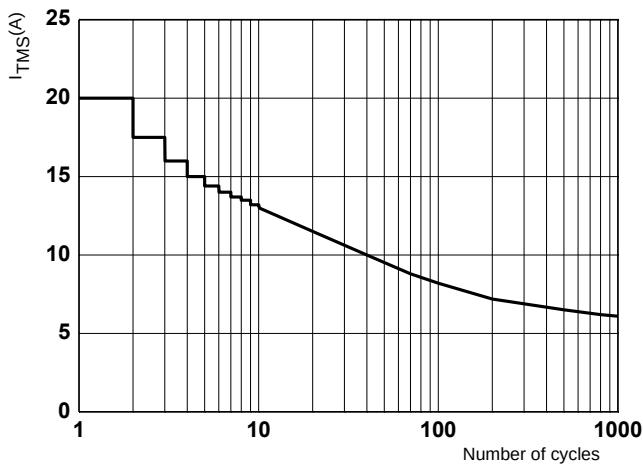


FIG.4: On-state characteristics (maximum values)

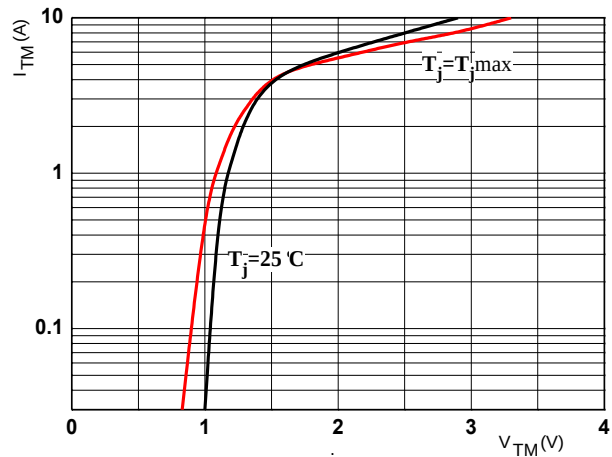


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

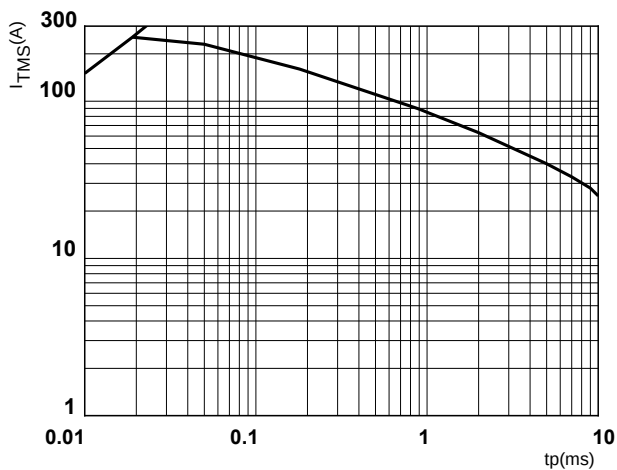
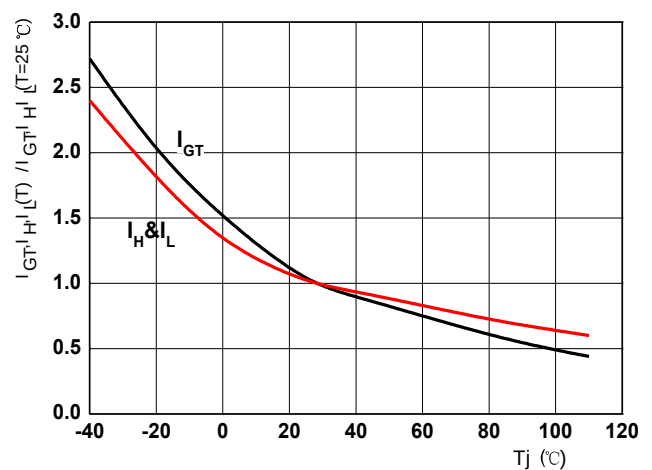
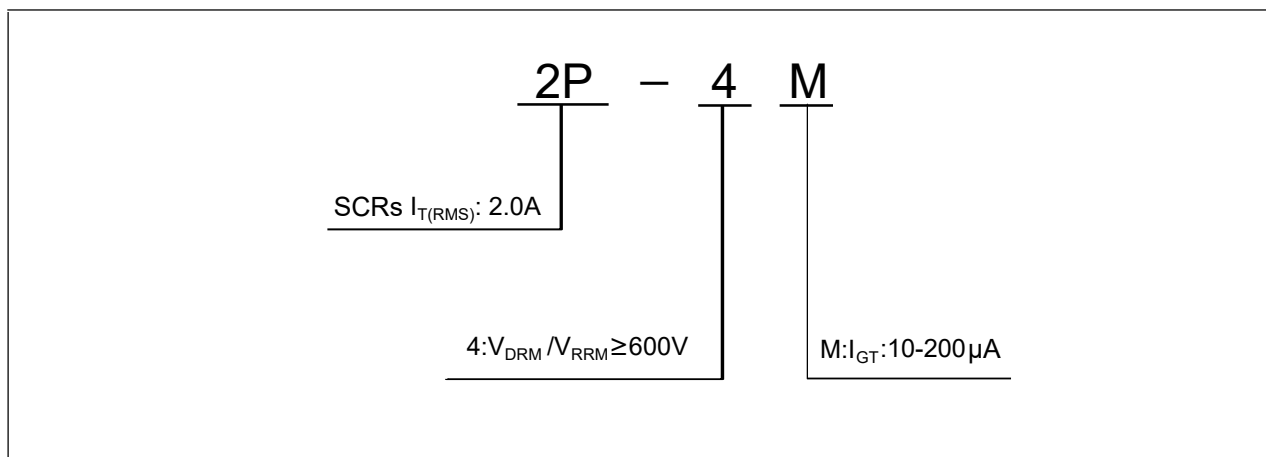


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Ordering Information



TO-92 Package Information

